TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L²-π-MOSV)

2SJ619

Switching Regulator and DC-DC Converter Applications Motor Drive Applications

• 4-V gate drive

• Low drain-source ON resistance: R_{DS} (ON) = 0.15Ω (typ.)

• High forward transfer admittance: $|Y_{fs}| = 7.7 \text{ S (typ.)}$

• Low leakage current: $I_{DSS} = -100 \,\mu\text{A}$ (max) ($V_{DS} = -100 \,\text{V}$)

• Enhancement-model: $V_{th} = -0.8 \text{ to } -2.0 \text{ V (VDS} = -10 \text{ V, ID} = -1 \text{ mA)}$

Maximum Ratings (Ta = 25°C)

Characte	eristics	Symbol	Rating	Unit	
Drain-source voltage	;	V_{DSS}	-100	V	
Drain-gate voltage (F	$R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	-100	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	-16	Α	
	Pulse (Note 1)	I _{DP}	-64	ı	
Drain power dissipat	ion (Tc = 25°C)	P_{D}	75	W	
Single pulse avalance	the energy (Note 2)	E _{AS}	292	mJ	
Avalanche current		I _{AR}	-16	Α	
Repetitive avalanche	e energy (Note 3)	E _{AR}	7.5	mJ	
Channel temperature	e	T _{ch}	150	°C	
Storage temperature	range	T _{stg}	-55 to150	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.67	°C/W

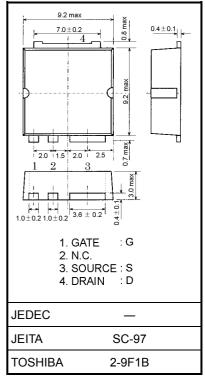
Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: $V_{DD} = -25$ V, $T_{ch} = 25^{\circ} C$ (initial), L = 1.84 mH, $R_G = 25~\Omega$, $I_{AR} = -16~A$

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

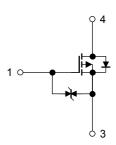
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.74 g (typ.)

Circuit Configuration



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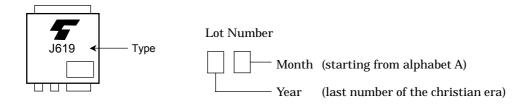
Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μΑ
Drain cut-OFF cu	rrent	I _{DSS}	$V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-100	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-100	_	_	V
Gate threshold vo	oltage	V _{th}	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	_	-2.0	٧
Drain-source ON resistance		Pro (ON)	$V_{GS} = -4 \text{ V}, I_D = -6 \text{ A}$	_	0.25	0.32	Ω
		R _{DS} (ON)	$V_{GS} = -10 \text{ V}, I_D = -6 \text{ A}$		0.15	0.21	
Forward transfer	admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -6 \text{ A}$	4.5	7.7		S
Input capacitance		C _{iss}		_	1100	_	pF
Reverse transfer capacitance		C _{rss}	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	210	_	
Output capacitance		Coss		_	440	_	
Switching time	Rise time	t _r	$V_{GS} \longrightarrow V_{OUT} \longrightarrow V_{OU$	_	18	_	
	Turn-ON time	t _{on}		_	30	_	
	Fall time	t _f			18	_	ns
	Turn-OFF time	t _{off}		_	65	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	48	_	nC
Gate-source charge		Q _{gs}	$V_{DD} \simeq -80 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -16 \text{ A}$	_	29	_	
Gate-drain ("miller") charge		Q _{gd}			19	_	

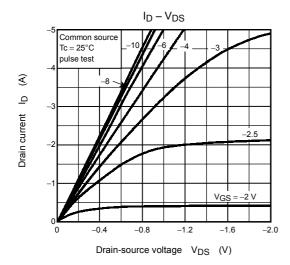
Source-Drain Ratings and Characteristics (Ta = 25°C)

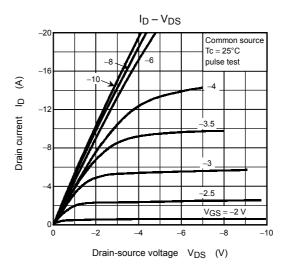
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	-16	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	-64	Α
Forward voltage (diode)	V_{DSF}	$I_{DR} = -16 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = -16 \text{ A}, V_{GS} = 0 \text{ V},$	_	160	_	μs
Reverse recovery charge	Q _{rr}	dl _{DR} /dt = 50 A/μs		0.5	_	μС

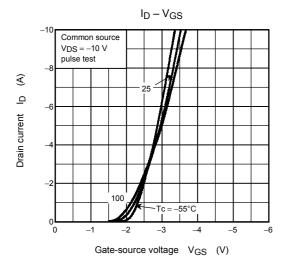
Marking

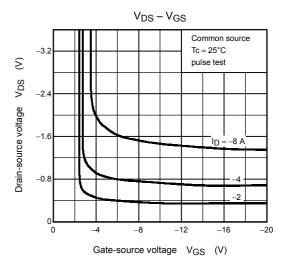


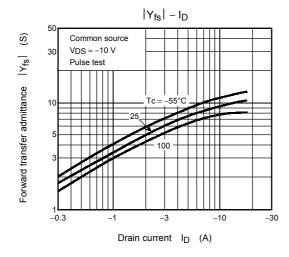
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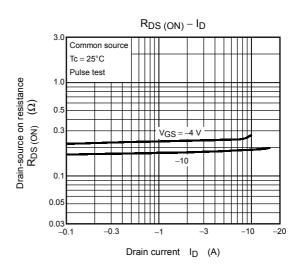




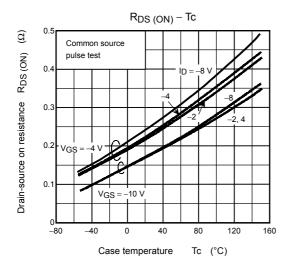


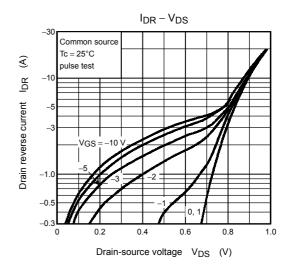


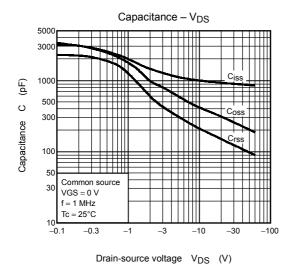


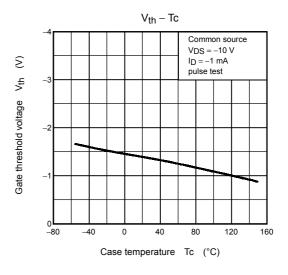


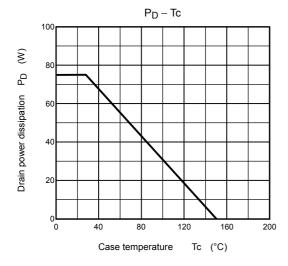
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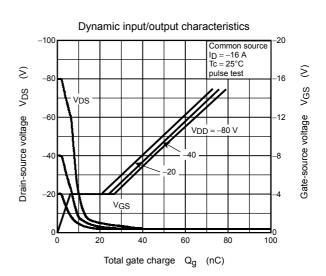


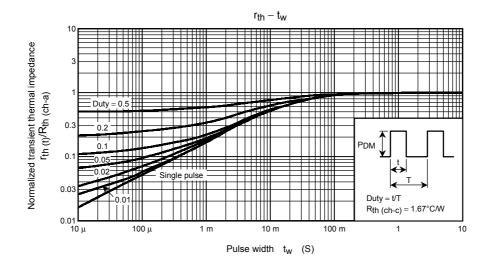


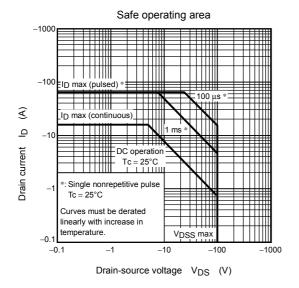


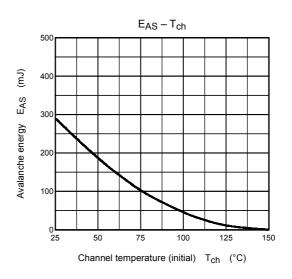


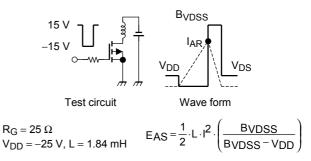












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